MSKSEMI 美森科













ESD

SS

MOV

GDI

PLED

MURSXXXT3G-MS

Product specification





SURFACE MOUNT ULTRAFAST POWER RECTIFIERS DIODES

VOLTAGE RANGE: 50 - 600V

CURRENT: 3.0A

Features

- Glass Passivated Die Construction
- Ideally Suited for Automatic Assembly
- Low Forward Voltage Drop, High Efficiency
- Low Power Loss
- Super-Fast Recovery Time
- Plastic Case Material has UL Flammability Classification Rating 94V-O

Mechanical Data

- Case: SMA/DO-214AA, Molded Plastic
- Terminals: Solder Plated, Solderable
- per MIL-STD-750, Method 2026
- Polarity: Cathode Band or Cathode Notch
- Weight: 0.21 grams (approx.)

Reference News

PACKAGE OUTLINE	Marking		
	MURS ***		
SMC(DO-214AB)	*** Representative VRRM		



Maximum Ratings and Electrical Characteristics TA = 25℃ unless otherwise specified Single

phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Characteristic		Symbol	MURS305 T3G-MS	MURS310 T3G-MS	MURS315 T3G-MS	MURS320 T3G-MS	MURS330 T3G-MS	MURS340 T3G-MS	MURS360 T3G-MS	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage		VRRM VRWM VR	50	100	150	200	300	400	600	V
RMS Reverse Voltage		VR(RMS)	35	70	105	140	210	280	420	V
Average Rectified Output Current	@T _L = 75°C	lo	3.0			Α				
	on-Repetitive Peak Forward Surge Current Bms Single half sine-wave superimposed on IFSM 100 led load (JEDEC Method)				А					
Forward Voltage @I _F = 3.0A		VFM	0.95 1.25 1.7			V				
Peak Reverse Current At Rated DC Blocking Voltage	@T _A = 25°C @T _A = 100°C	lгм	5.0 500			μA				
Reverse Recovery Time (Note 1)	erse Recovery Time (Note 1) trr 35			nS						
Typical Junction Capacitance (Note	2) C _j 45		pF							
Typical Thermal Resistance (Note 3)		16			°C/W					
Operating and Storage Temperature Range		Тj, Tsтg	-65 to +150				°C			

Note:

- 1. Measured with $I_F=0.5A$, $I_R=1.0A$, $I_{rr}=0.25A$. See figure 5. 2. Measured at 1.0 MHz and applied reverse voltage of 4.0 V DC.
- 3. Mounted on P.C. Board with 8.0mm² land area.



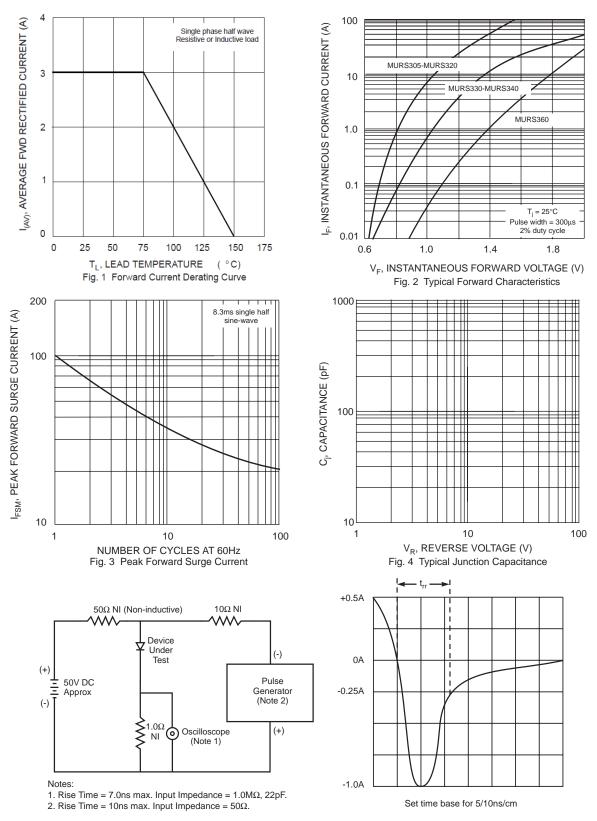
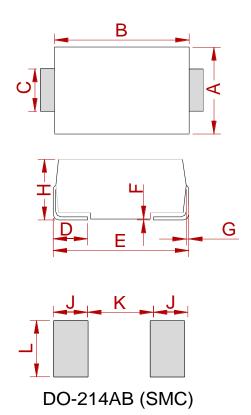


Fig. 5 Reverse Recovery Time Characteristic and Test Circuit



PACKAGE MECHANICAL DATA



	Dimensions				
Ref.	Millimeters		Inches		
	Min.	Max.	Min.	Max.	
Α	5.75	6.25	0.226	0.246	
В	6.90	7.40	0.272	0.291	
С	2.75	3.25	0.108	0.128	
D	0.95	1.52	0.037	0.060	
E	7.70	8.20	0.303	0.323	
F	0.051	0.203	0.002	0.008	
G	0.15	0.31	0.006	0.012	
Н	2.15	2.62	0.085	0.103	
J	2.40		0.094		
K		4.20		0.165	
L	3.30		0.130		

REEL SPECIFICATION

P/N	PKG	QTY
MURSXXXT3G-MS	SMC	2500



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